

IN THE SPECIFICATION:

Please amend paragraph [0036] as follows:

[0036] The present invention is directed to a method for creating depressions in a semiconductor substrate or film using laser machining, or ablation, processes. The depressions define traces or lines for ~~signals~~ signal lines, power and ground lines, and other elongated conductive elements utilized for defining electrical pathways in a semiconductor device. The method requires fewer processing steps than conventional mask and etch techniques and enables the creation of lines or traces substantially simultaneously with discrete conductive structures, such as vias or bond pads. Further, the process offers a lower cost alternative to conventional damascene and dual damascene processes and enables the formation of elongated conductive elements and discrete conductive structures of varying shapes to maximize use of the substrate or film. An exemplary application of the technology of the present invention is for creating electrical pathways to form a redistribution layer in wafer level packaging. The particular embodiments described herein are intended in all respects to be illustrative rather than restrictive. Other and further embodiments will become apparent to those of ordinary skill in the art to which the present invention pertains without departing from its ~~scope~~ scope.

Please amend paragraph [0043] as follows:

[0043] A representative laser fluence for forming the trace depressions 108 through a semiconductor substrate 104 (e.g., a silicon wafer) having a thickness of about 28 mils (725 μm), is from about 2 to about ~~10 watts/opening~~ 10 watts per opening at a pulse duration of 20-25 NS, and at a repetition rate of up to several thousand per second. The wavelength of the focused laser beam 110 may be a standard UV wavelength (e.g., 355 nm) or green wavelength (e.g., 1064 nm-532 nm). By way of example, the width of the trace depressions 108 can be from about 10 μm to about 2 mils or greater.

Please amend paragraph [0063] as follows:

[0063] Referring initially to FIG. 5A, a cross-sectional view of an intermediate structure 118 in the fabrication of a semiconductor device structure 120 having a plurality of

traces 122 formed in a surface 123 of the semiconductor substrate 124 thereof is shown. As shown in FIG. 5B, a desired pattern of elongated conductive element precursors in the form of one or more trace depressions 126 and one or more discrete conductive structure precursors, *e.g.*, vias 128, may be formed in the surface 123 of the semiconductor substrate 124 using a focused laser beam 130. ~~beam 130~~. The trace depressions 126 and vias 128 may be of any size, shape and depth suitable to define the desired conductive pathway. The vias 128 may extend through the full thickness of the semiconductor substrate 124 (embodiment not shown), or may extend into the semiconductor substrate 124 a depth less than the full thickness thereof as shown.